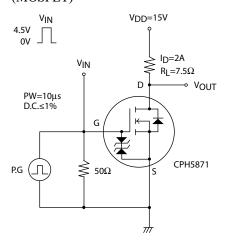
#### **Electrical Characteristics** at Ta = 25°C

Danamataa	Symbol	Conditions	Value			11-4
Parameter		Conditions	min	typ	max	Unit
[MOSFET]						
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			٧
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA 0.4			1.3	>
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	2.0	3.4		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V		40	52	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		53	74	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.5A, V <sub>GS</sub> =1.8V		82	132	mΩ
Input Capacitance	Ciss			430		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		59		pF
Reverse Transfer Capacitance	Crss			38		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			10		ns
Rise Time	t <sub>r</sub>	Con an ariffed Took Oinsuit		41		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		36		ns
Fall Time	t <sub>f</sub>			37		ns
Total Gate Charge	Qg	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.5A		4.7		nC
Gate to Source Charge	Qgs			0.8		nC
Gate to Drain "Miller" Charge	Qgd			1.1		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V		0.8	1.2	V
[SBD]						
Reverse Voltage	VR	I <sub>R</sub> =0.5mA	30			V
Forward Voltage	V <sub>F1</sub>	I <sub>F</sub> =0.7A		0.45	0.5	V
	V <sub>F2</sub>	I <sub>F</sub> =1A		0.48	0.53	V
Reverse Current	IR	V <sub>R</sub> =16V			15	μА
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz, 1cycle		27		pF
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> =100mA, See specified Test Circuit			10	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

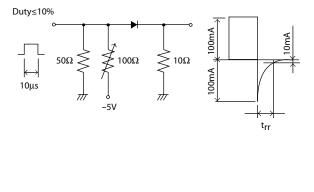
# **Switching Time Test Circuit**

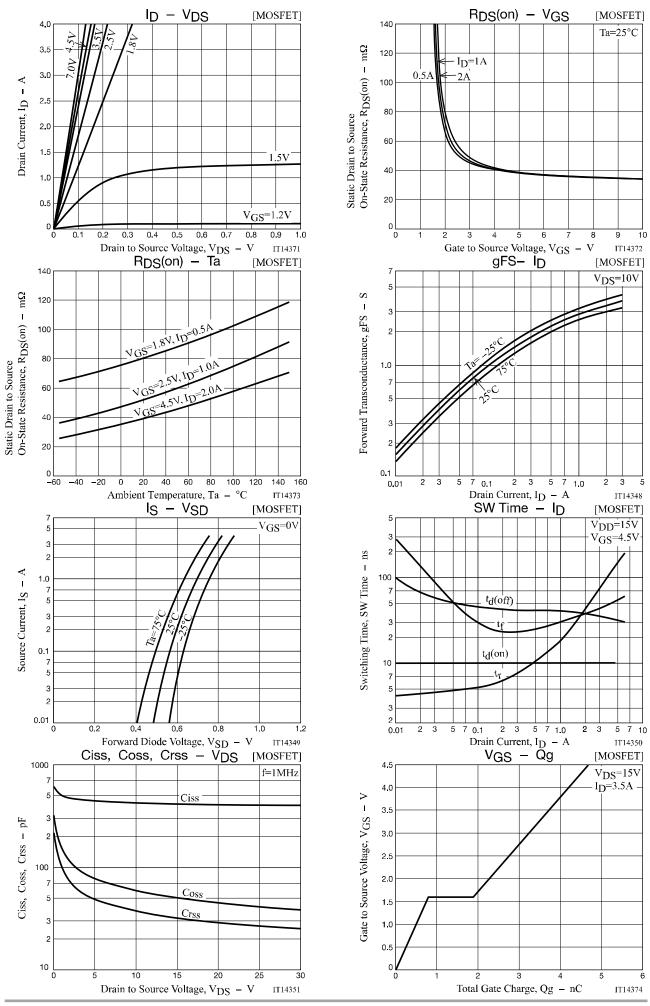
# (MOSFET)

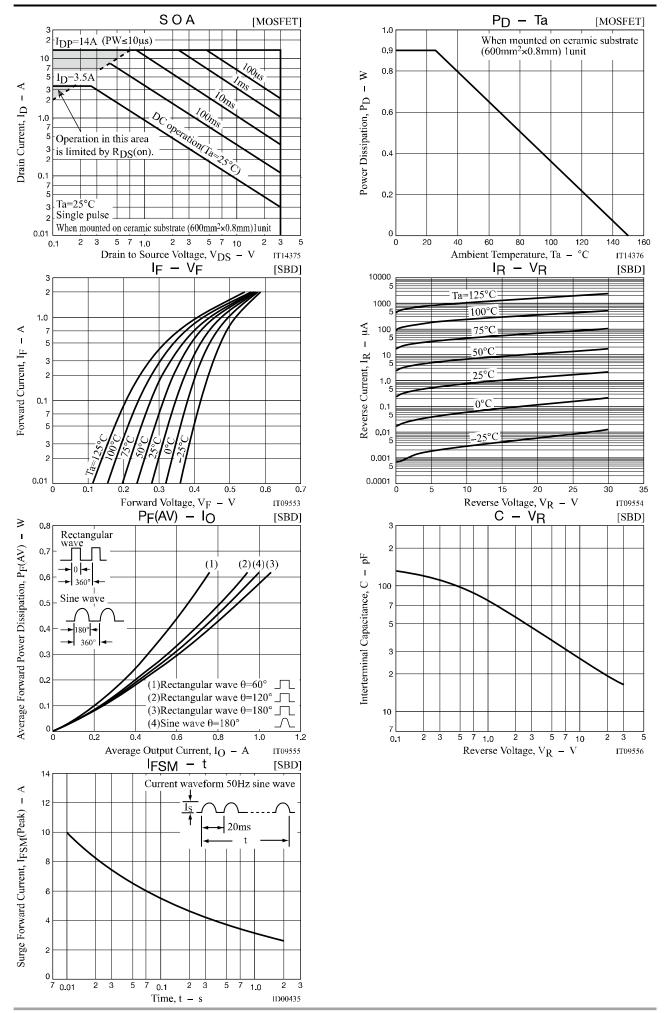


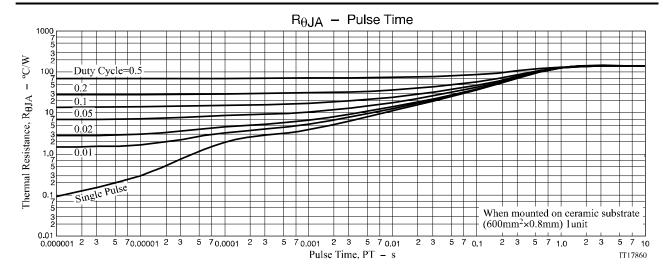
# trr Test Circuit

(SBD)









### **Package Dimensions**

CPH5871-TL-H / CPH5871-TL-W

#### CPH<sub>5</sub>

CASE 318BC ISSUE O

unit: mm

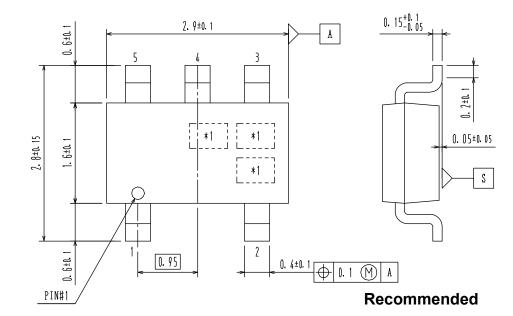
1: Cathode

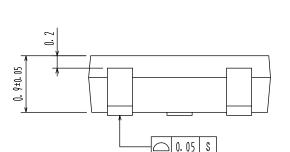
2: Drain

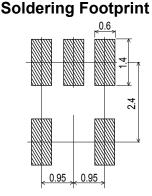
3: Gate

4: Source

5: Anode







\*1:Lot indication

#### ORDERING INFORMATION

Device	Package	Shipping	Note
CPH5871-TL-H	CPH5	3,000 pcs. / Tape & Reel	Pb-Free
CPH5871-TL-W	SC-74A, SOT-25	3,000 pos. / Tape & Reel	and Halogen Free

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the CPH5871 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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